



《风光欣》技术资料

A733

PNP EPITAXIAL SILICON TRANSISTOR

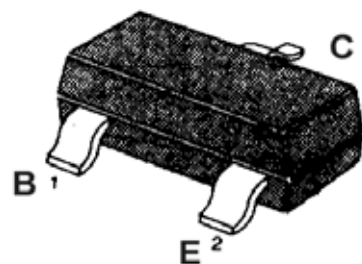
*Complement to **C945**

*Collector-Base Voltage $V_{CBO} = -60V$

ABSOLUTE MAXIMUM RATINGS($T_A = 25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter -Base Voltage	V_{EBO}	-5	V
Collector Current	I_c	-150	mA
Collector Dissipation	P_c	200	mW
Junction Temperature	T_J	150	

SOT-23



ELECTRICAL CHARACTERISTICS($T_A = 25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c = -100 \mu A, I_E = 0$	-60			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c = -10mA, I_B = 0$	-50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -10 \mu A, I_c = 0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -60V, I_E = 0$			-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_c = 0$			-0.1	μA
DC Current Gain	H_{FE}	$V_{CE} = -6V, I_c = -1mA$	40		700	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = -100mA, I_B = -10mA$		-0.18	-0.3	V
Base-Emitter On Voltage	$V_{BE(sat)}$	$V_{CE} = -6V, I_c = -1mA$	-0.5	-0.62	-0.8	V
Current Gain-Bandwidth Product	f_T	$V_{CE} = -6V, I_c = -10mA$	50	180		MHz
Output Capacitance	C_{OB}	$f = 1MHz, V_{CB} = -10V, I_E = 0$		2.8		pF
Noise Figure	NF	$V_{CE} = -6V, I_c = -0.3mA$				
		$f = 1KHZ, R_s = 10K$		6.0	20.0	dB

Hfe CLASSIFICATION

Classification	R	O	Y	G	L
HFE	40-80	70-140	120-240	200-400	350-700